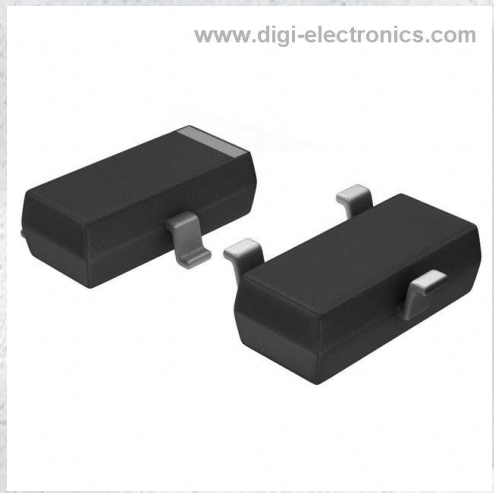
AOSS32334C Datasheet



https://www.DiGi-Electronics.com

DiGi Electronics Part Number	AOSS32334C-DG
Manufacturer	Alpha & Omega Semiconductor Inc.
Manufacturer Product Number	AOSS32334C
Description	MOSFET N-CH 30V 6.2A SOT23-3
Detailed Description	N-Channel 30 V 6.2A (Ta) 1.3W (Ta) Surface Mount SOT-23-3

Tel: +00 852-30501935

RFQ Email: Info@DiGi-Electronics.com

Purchase and inquiry

Manufacturer Product Number:	Manufacturer:
AOSS32334C	Alpha & Omega Semiconductor Inc.
Series:	Product Status:
-	Active
FET Type:	Technology:
N-Channel	MOSFET (Metal Oxide)
Drain to Source Voltage (Vdss):	Current - Continuous Drain (Id) @ 25°C:
30 V	6.2A (Ta)
Drive Voltage (Max Rds On, Min Rds On):	Rds On (Max) @ Id, Vgs:
4.5V, 10V	20mOhm @ 6.2A, 10V
Vgs(th) (Max) @ Id:	Gate Charge (Qg) (Max) @ Vgs:
2.3V @ 250µA	20 nC @ 10 V
Vgs (Max):	Input Capacitance (Ciss) (Max) @ Vds:
±20V	600 pF @ 15 V
FET Feature:	Power Dissipation (Max):
-	1.3W (Ta)
Operating Temperature:	Mounting Type:
-55°C ~ 150°C (TJ)	Surface Mount
Supplier Device Package:	Package / Case:
SOT-23-3	3-SMD, SOT-23-3 Variant
Base Product Number:	
AOSS323	

Environmental & Export classification

RoHS Status:	Moisture Sensitivity Level (MSL):
ROHS3 Compliant	1 (Unlimited)
REACH Status:	ECCN:
REACH Unaffected	EAR99
HTSUS:	
8541.29.0095	

ALPHA & OMEGA SEMICONDUCTOR

AOSS32334C

30V N-Channel MOSFET

General Description

- Trench Power MOSFET technology
- Low $R_{DS(ON)}$
- Low Gate Charge
- RoHS and Halogen-Free Compliant

Applications

- Ideal for Load Switch

Product Summary

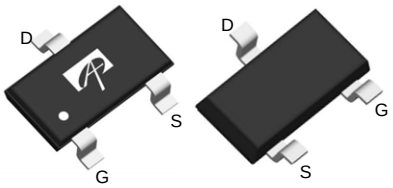
V_{DS}	30V
I_D (at V_{GS}=4.5V)	6.2A
$R_{DS(ON)}$ (at V_{GS}=10V)	< 20mΩ
$R_{DS(ON)}$ (at V_{GS}=4.5V)	< 26mΩ

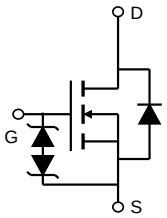
ESD protection

Green Product

SOT23

Top View **Bottom View**





Orderable Part Number	Package Type	Form	Minimum Order Quantity
AOSS32334C	SOT23-3	Tape & Reel	3000

Absolute Maximum Ratings T_A=25°C unless otherwise noted

Parameter		Symbol	Maximum	Units
Drain-Source Voltage		V_{DS}	30	V
Gate-Source Voltage		V_{GS}	±20	V
Continuous Drain Current	T_A=25°C	I_D	6.2	A
	T_A=70°C		4.8	
Pulsed Drain Current [C]		I_{DM}	40	
Power Dissipation [B]	T_A=25°C	P_D	1.3	W
	T_A=70°C		0.8	
Junction and Storage Temperature Range		T_J, T_{STG}	-55 to 150	°C

Thermal Characteristics

Parameter		Symbol	Typ	Max	Units
Maximum Junction-to-Ambient [A]	t ≤ 10s	$R_{\theta JA}$	70	90	°C/W
Maximum Junction-to-Ambient [A D]	Steady-State		100	125	°C/W
Maximum Junction-to-Lead	Steady-State	$R_{\theta JL}$	63	80	°C/W

Electrical Characteristics (T_J=25°C unless otherwise noted)

Symbol	Parameter	Conditions	Min	Typ	Max	Units
STATIC PARAMETERS						
BV_{DSS}	Drain-Source Breakdown Voltage	ID=250µA, VGS=0V	30			V
I_{DSS}	Zero Gate Voltage Drain Current	V_{DS}=30V, V_{GS}=0V			1	µA
		T_J=55°C			5	
I_{GSS}	Gate-Body leakage current	V_{DS}=0V, V_{GS}=±20V			±10	µA
$V_{GS(th)}$	Gate Threshold Voltage	V_{DS}=$V_{GS,}$ I_D=250µA	1.3	1.8	2.3	V
$R_{DS(ON)}$	Static Drain-Source On-Resistance	V_{GS}=10V, I_D=6.2A		16	20	mΩ
		T_J=125°C		24	30	
		V_{GS}=4.5V, I_D=5.5A		20	26	mΩ
g_{FS}	Forward Transconductance	V_{DS}=5V, I_D=6.2A		33		S
V_{SD}	Diode Forward Voltage	I_S=1A, V_{GS}=0V		0.7	1	V
I_S	Maximum Body-Diode Continuous Current				2	A
DYNAMIC PARAMETERS						
C_{iss}	Input Capacitance	V_{GS}=0V, V_{DS}=15V, f=1MHz		600		pF
C_{oss}	Output Capacitance			70		pF
C_{rss}	Reverse Transfer Capacitance			60		pF
R_g	Gate resistance	f=1MHz	1.2	2.4	3.6	Ω
SWITCHING PARAMETERS						
Q_g(10V)	Total Gate Charge	V_{GS}=10V, V_{DS}=15V, I_D=6.2A		12	20	nC
Q_g(4.5V)	Total Gate Charge			6	12	nC
Q_{gs}	Gate Source Charge			2.2		nC
Q_{gd}	Gate Drain Charge			2.5		nC
$t_{D(on)}$	Turn-On DelayTime	V_{GS}=10V, V_{DS}=15V, R_L=2.42Ω, R_{GEN}=3Ω		4.5		ns
t_r	Turn-On Rise Time			4		ns
$t_{D(off)}$	Turn-Off DelayTime			20		ns
t_f	Turn-Off Fall Time			4		ns
t_{rr}	Body Diode Reverse Recovery Time	I_F=6.2A, di/dt=500A/µs		5		ns
Q_{rr}	Body Diode Reverse Recovery Charge	I_F=6.2A, di/dt=500A/µs		6		nC

A. The value of $R_{\theta JA}$ is measured with the device mounted on 1in² FR-4 board with 2oz. Copper, in a still air environment with T_A =25° C. The value in any given application depends on the user's specific board design.
B. The power dissipation P_D is based on $T_{J(MAX)}$=150° C, using ≤ 10s junction-to-ambient thermal resistance.
C. Repetitive rating, pulse width limited by junction temperature $T_{J(MAX)}$=150° C. Ratings are based on low frequency and duty cycles to keep initialT_J=25° C.
D. The $R_{\theta JA}$ is the sum of the thermal impedance from junction to lead $R_{\theta JL}$ and lead to ambient.
E. The static characteristics in Figures 1 to 6 are obtained using <300µs pulses, duty cycle 0.5% max.
F. These curves are based on the junction-to-ambient thermal impedance which is measured with the device mounted on 1in² FR-4 board with 2oz. Copper, assuming a maximum junction temperature of $T_{J(MAX)}$=150° C. The SOA curve provides a single pulse rating.

TYPICAL ELECTRICAL AND THERMAL CHARACTERISTICS

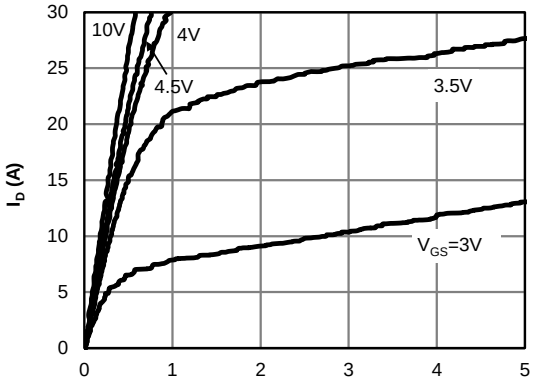


Figure 1: On-Region Characteristics (Note E)

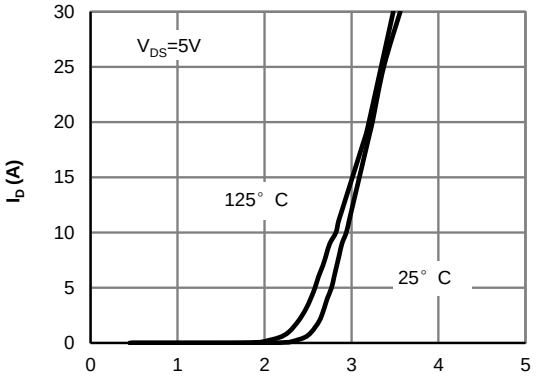


Figure 2: Transfer Characteristics (Note E)

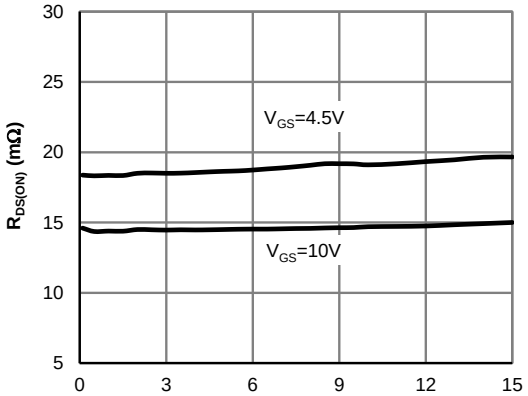


Figure 3: On-Resistance vs. Drain Current and Gate Voltage (Note E)

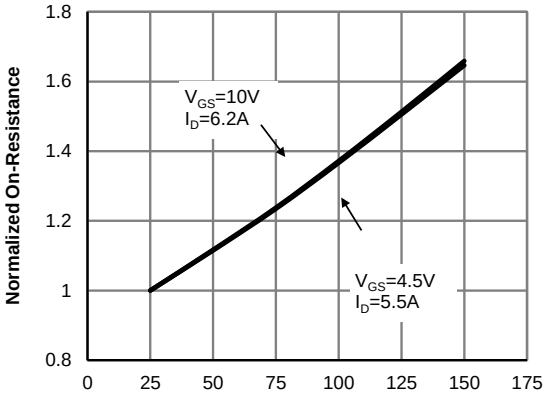


Figure 4: On-Resistance vs. Junction Temperature (Note E)

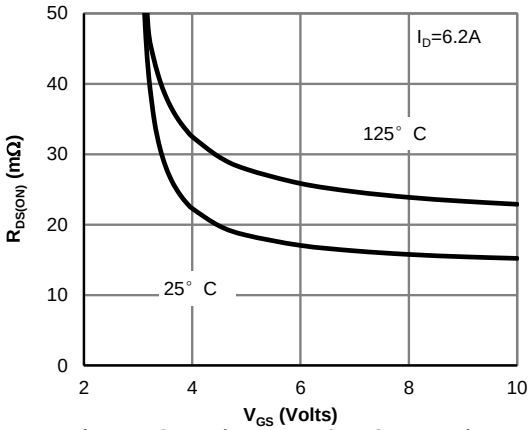


Figure 5: On-Resistance vs. Gate-Source Voltage (Note E)

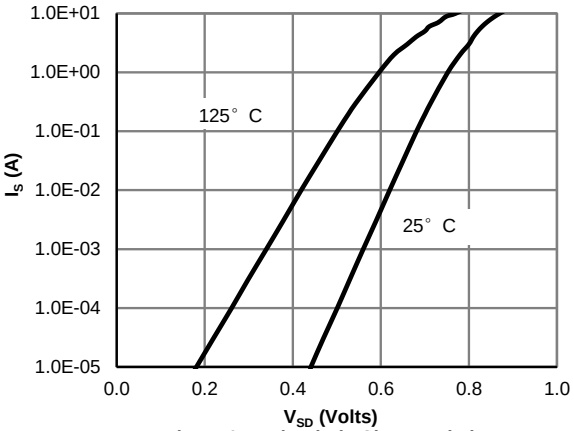


Figure 6: Body-Diode Characteristics (Note E)

TYPICAL ELECTRICAL AND THERMAL CHARACTERISTICS

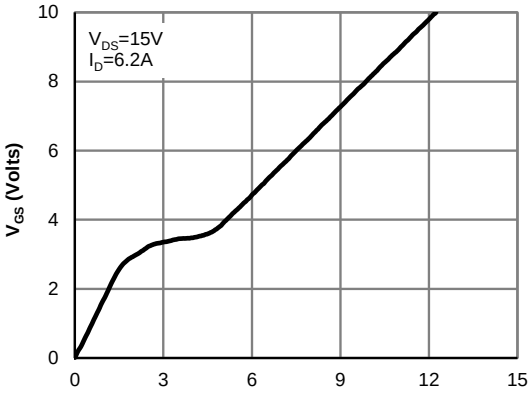


Figure 7: Gate-Charge Characteristics

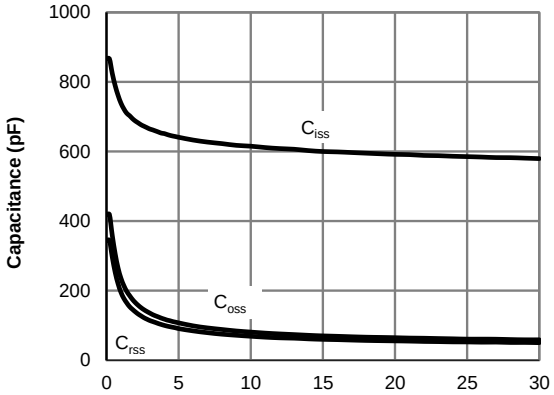
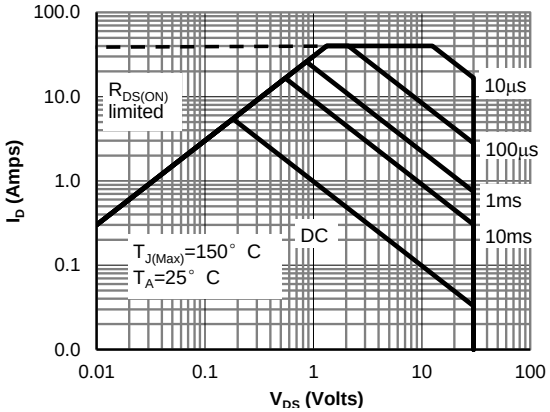


Figure 8: Capacitance Characteristics



V_{GS}> or equal to 4.5V
Figure 9: Maximum Forward Biased Safe Operating Area (Note F)

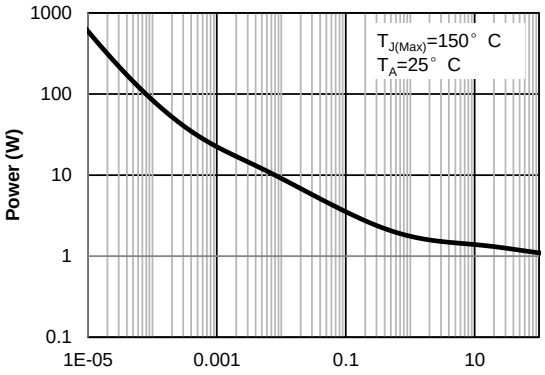


Figure 10: Single Pulse Power Rating Junction-to-Ambient (Note F)

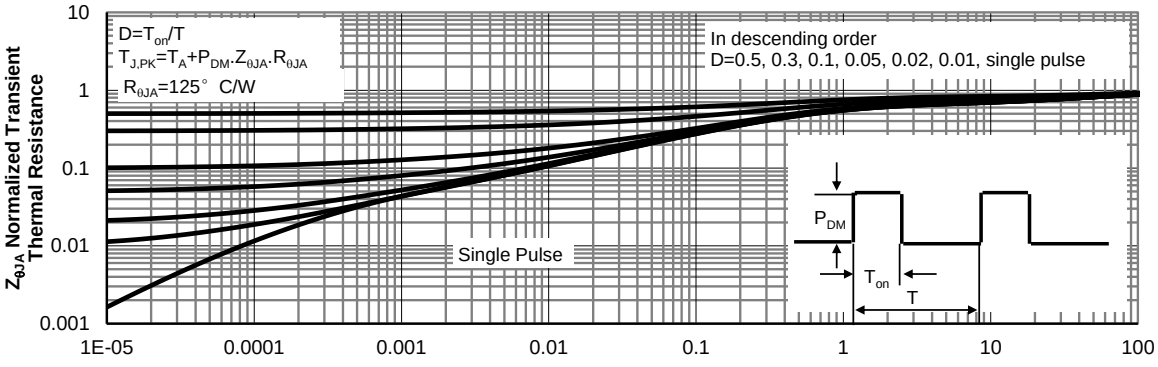


Figure 11: Normalized Maximum Transient Thermal Impedance (Note F)

Figure A: Gate Charge Test Circuit & Waveforms

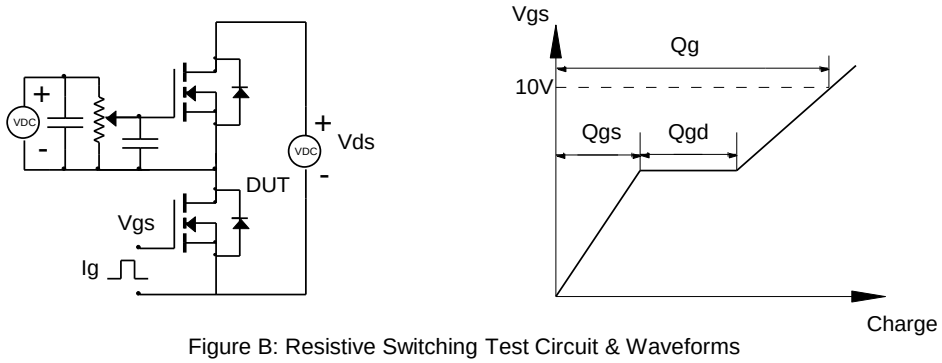


Figure B: Resistive Switching Test Circuit & Waveforms

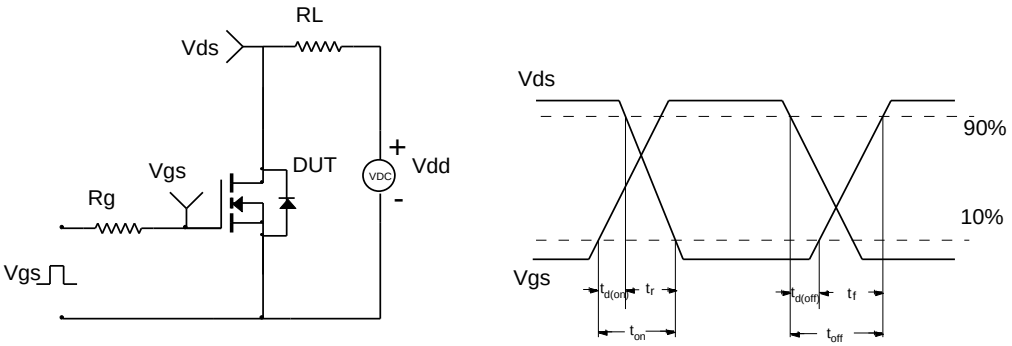


Figure C: Unclamped Inductive Switching (UIS) Test Circuit & Waveforms

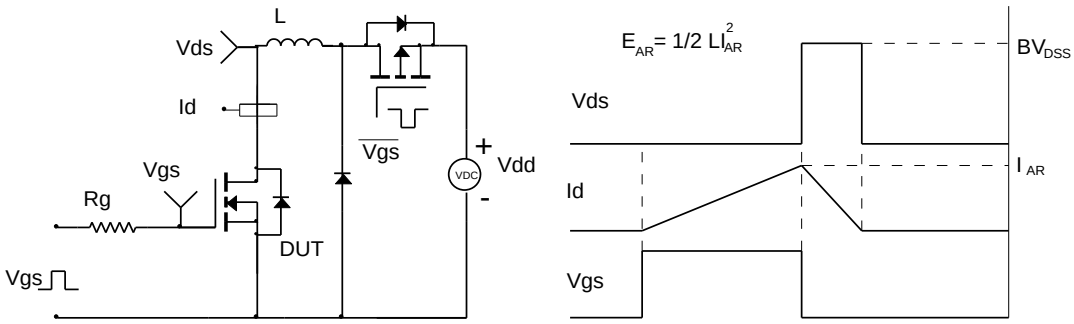
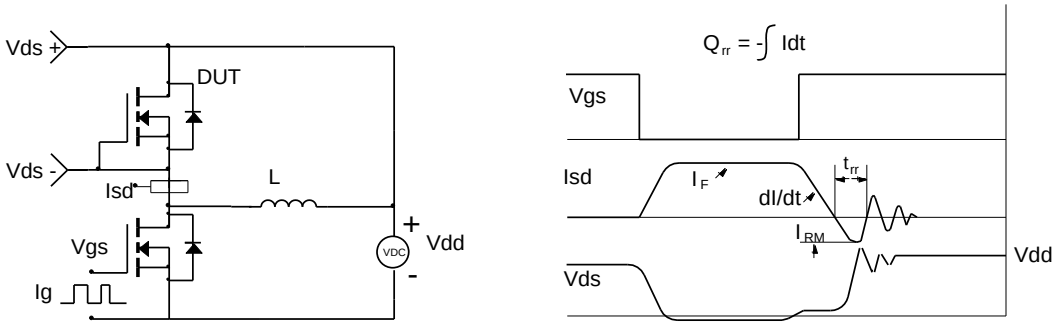


Figure D: Diode Recovery Test Circuit & Waveforms



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